



## REVISION HISTORY

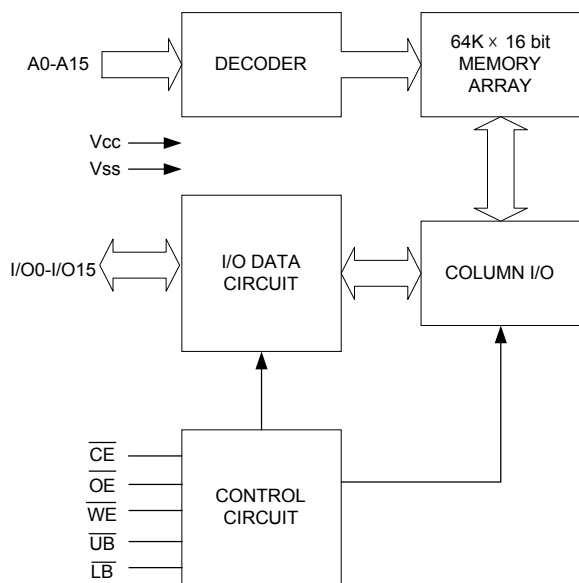
REVISION	DESCRIPTION	Draft Date
Preliminary Rev. 0.4	Original.	Mar, 2001
Preliminary Rev. 0.5	1.The symbols CE# and OE# and WE# are revised as. $\overline{CE}$ and $\overline{OE}$ and $\overline{WE}$ . 2.Separate Industrial and Commercial SPEC. 3.Add access time 15ns range. 4.Delete SOJ package.	Aug 31,2001
Rev. 1.0	1.Revised CMOS low power operating : Operating current : 195→150mA (max.) Standby current : 30→3mA (max.) 2.Revised power supply : 3.0~3.6V→3.15~3.6V 3.Revised DC CHARACTERISTICE $I_{CC}$ -8ns (max) : 200→150mA $I_{CC}$ -10ns (max) : 195→120mA $I_{CC}$ -12ns (max) : 190→100mA $I_{CC}$ -15ns (max) : 150→80 mA $I_{SB}$ (max) : 30→10mA $I_{SB1}$ (max) : 10→3mA $I_{SB1}$ (max)<1 mA for special order	Nov 4,2002



### FEATURES

- Fast access time :
  - 8ns for Vcc=3.15V~3.6V
  - 10/12/15ns for Vcc=3.0V~3.6V
- CMOS low power operating :
  - Operating current : 150mA (max.)
  - Standby current : 3mA (max.)
- Single 3.15~3.6V power supply
- Operating temperature :
  - Commercial : 0°C~70°C
- All TTL compatible inputs and outputs
- Fully static operation
- Three state outputs
- Data byte control :  $\overline{LB}$  (I/O0~I/O7)  
 $\overline{UB}$  (I/O8~I/O15)
- Package : 44-pin 400mil TSOP II

### FUNCTIONAL BLOCK DIAGRAM



### GENERAL DESCRIPTION

The UT61L6416 is a 1,048,576-bit high speed CMOS static random access memory organized as 65,536 words by 16 bits.

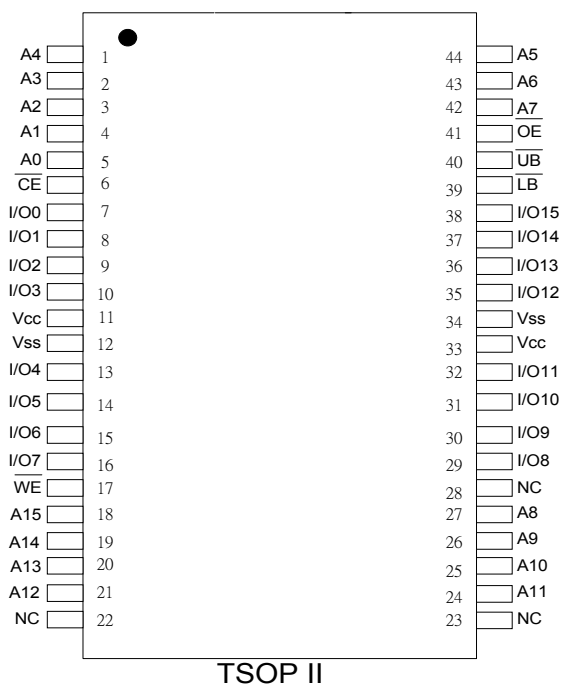
The UT61L6416 operates from a single 3.15 ~ 3.6V power supply and all inputs and outputs are fully TTL compatible.

The UT61L6416 is designed for lower and upper byte access by data byte control. ( $\overline{LB}$   $\overline{UB}$ )

### PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0 - A15	Address Inputs
I/O0 - I/O15	Data Inputs/Outputs
$\overline{CE}$	Chip Enable Input
$\overline{WE}$	Write Enable Input
$\overline{OE}$	Output Enable Input
$\overline{LB}$	Lower Byte Control
$\overline{UB}$	Upper Byte Control
V <sub>CC</sub>	Power Supply
V <sub>SS</sub>	Ground
NC	No Connection

### PIN CONFIGURATION





**ABSOLUTE MAXIMUM RATINGS\***

PARAMETER	SYMBOL	RATING	UNIT
Terminal Voltage with Respect to V <sub>SS</sub>	V <sub>TERM</sub>	-0.5 to 4.6	V
Operating Temperature	T <sub>A</sub>	0 to 70	°C
Storage Temperature	T <sub>STG</sub>	-65 to 150	°C
Power Dissipation	P <sub>D</sub>	1	W
DC Output Current	I <sub>OUT</sub>	50	mA
Soldering Temperature (under 10 secs)	T <sub>solder</sub>	260	°C

\*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

**TRUTH TABLE**

MODE	CE	OE	WE	LB	UB	I/O OPERATION		SUPPLY CURRENT
						I/O0-I/O7	I/O8-I/O15	
Standby	H	X	X	X	X	High - Z	High - Z	I <sub>SB</sub> , I <sub>SB1</sub>
	X	X	X	H	H			
Output Disable	L	H	H	L	X	High - Z	High - Z	I <sub>CC</sub>
	L	H	H	X	L	High - Z	High - Z	
Read	L	L	H	L	H	D <sub>OUT</sub>	High - Z	I <sub>CC</sub>
	L	L	H	H	L	High - Z	D <sub>OUT</sub>	
	L	L	H	L	L	D <sub>OUT</sub>	D <sub>OUT</sub>	
Write	L	X	L	L	H	D <sub>IN</sub>	High - Z	I <sub>CC</sub>
	L	X	L	H	L	High - Z	D <sub>IN</sub>	
	L	X	L	L	L	D <sub>IN</sub>	D <sub>IN</sub>	

Note: H = V<sub>IH</sub>, L = V<sub>IL</sub>, X = Don't care.

**DC ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 0°C to 70°C)**

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Power Voltage	V <sub>CC</sub>	8	3.15	3.3	3.6	V	
		10/12/15	3.0	3.3	3.6	V	
Input High Voltage	V <sub>IH</sub>		2.0	-	V <sub>CC</sub> +0.3	V	
Input Low Voltage	V <sub>IL</sub>		-0.3	-	0.8	V	
Input Leakage Current	I <sub>LI</sub>	V <sub>SS</sub> ≤ V <sub>IN</sub> ≤ V <sub>CC</sub>	-2	-	2	μA	
Output Leakage Current	I <sub>LO</sub>	V <sub>SS</sub> ≤ V <sub>IO</sub> ≤ V <sub>CC</sub> ; Output Disable	-2	-	2	μA	
Output High Voltage	V <sub>OH</sub>	I <sub>OH</sub> = -4mA	2.4	-	-	V	
Output Low Voltage	V <sub>OL</sub>	I <sub>OL</sub> = 8mA	-	-	0.4	V	
Operating Power Supply Current	I <sub>CC</sub>	Cycle time=min, 100%duty I/O=0mA, CE = V <sub>IL</sub>	8	-	-	150	mA
			10	-	-	120	mA
			12	-	-	100	mA
			15	-	-	80	mA
Standby Current (TTL)	I <sub>SB</sub>	CE = V <sub>IH</sub> , other pins = V <sub>IL</sub> or V <sub>IH</sub>	-	-	10	mA	
Standby Current (CMOS)	I <sub>SB1</sub>	CE = V <sub>CC</sub> -0.2V, other pins at 0.2V or V <sub>CC</sub> -0.2V	-	-	3*	mA	

\* I<sub>SB1</sub> < 1mA for special order or requirement.

**CAPACITANCE** ( $T_A=25^\circ\text{C}$ ,  $f=1.0\text{MHz}$ )

PARAMETER	SYMBOL	MIN.	MAX	UNIT
Input Capacitance	$C_{IN}$	-	6	pF
Input/Output Capacitance	$C_{I/O}$	-	8	pF

Note : These parameters are guaranteed by device characterization, but not production tested.

**AC TEST CONDITIONS**

Input Pulse Levels	0V to 3.0V
Input Rise and Fall Times	3ns
Input and Output Timing Reference Levels	1.5V
Output Load	$C_L = 30\text{pF}$ , $I_{OH}/I_{OL} = -4\text{mA} / 8\text{mA}$

**AC ELECTRICAL CHARACTERISTICS** ( $T_A = 0^\circ\text{C}$  to  $70^\circ\text{C}$ )**(1) READ CYCLE**

PARAMETER	SYMBOL	UT61L6416 -8		UT61L6416 -10		UT61L6416 -12		UT61L6416 -15		UNIT
		$V_{CC}=3.15\sim 3.6$		$V_{CC}=3.0\sim 3.6$		$V_{CC}=3.0\sim 3.6$		$V_{CC}=3.0\sim 3.6$		
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	$t_{RC}$	8	-	10	-	12	-	15	-	ns
Address Access Time	$t_{AA}$	-	8	-	10	-	12	-	15	ns
Chip Enable Access Time	$t_{ACE}$	-	8	-	10	-	12	-	15	ns
Output Enable Access Time	$t_{OE}$	-	4	-	5	-	6	-	7	ns
Chip Enable to Output in Low Z	$t_{CLZ}^*$	3	-	3	-	3	-	3	-	ns
Output Enable to Output in Low Z	$t_{OLZ}^*$	0	-	0	-	0	-	0	-	ns
Chip Disable to Output in High Z	$t_{CHZ}^*$	-	4	-	5	-	6	-	7	ns
Output Disable to Output in High Z	$t_{OHZ}^*$	-	4	-	5	-	6	-	7	ns
Output Hold from Address Change	$t_{OH}$	3	-	3	-	3	-	3	-	ns
$\overline{LB}$ , $\overline{UB}$ Access Time	$t_{BA}$	-	4	-	5	-	6	-	7	ns
$\overline{LB}$ , $\overline{UB}$ to High Z Output	$t_{BHZ}$	-	4	-	5	-	6	-	7	ns
$\overline{LB}$ , $\overline{UB}$ to Low Z Output	$t_{BLZ}$	0	-	0	-	0	-	0	-	ns

**(2) WRITE CYCLE**

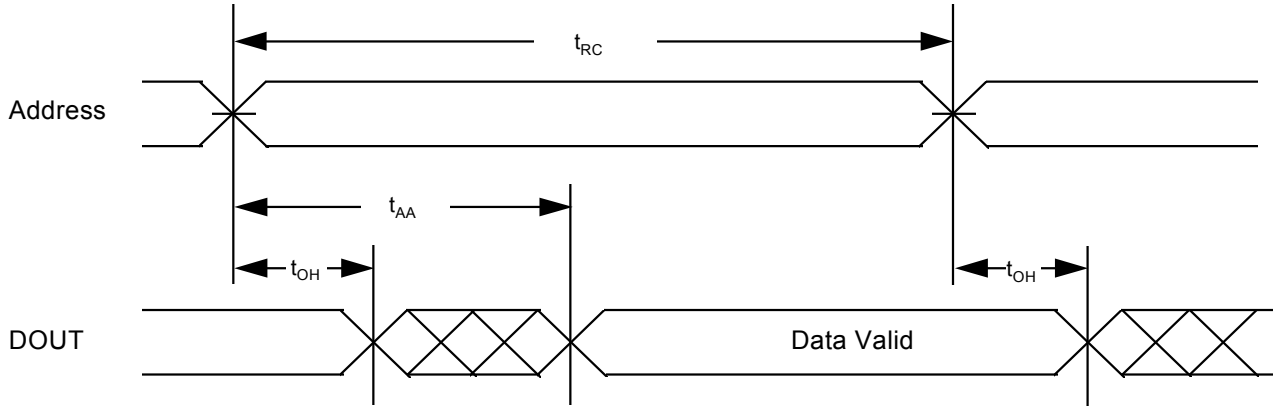
PARAMETER	SYMBOL	UT61L6416 -8		UT61L6416 -10		UT61L6416 -12		UT61L6416 -15		UNIT
		$V_{CC}=3.15\sim 3.6$		$V_{CC}=3.0\sim 3.6$		$V_{CC}=3.0\sim 3.6$		$V_{CC}=3.0\sim 3.6$		
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Write Cycle Time	$t_{WC}$	8	-	10	-	12	-	15	-	ns
Address Valid to End of Write	$t_{AW}$	7	-	8	-	9	-	10	-	ns
Chip Enable to End of Write	$t_{CW}$	7	-	8	-	9	-	10	-	ns
Address Set-up Time	$t_{AS}$	0	-	0	-	0	-	0	-	ns
Write Pulse Width	$t_{WP}$	7	-	8	-	9	-	10	-	ns
Write Recovery Time	$t_{WR}$	0	-	0	-	0	-	0	-	ns
Data to Write Time Overlap	$t_{DW}$	5.5	-	6	-	7	-	8	-	ns
Data Hold from End of Write Time	$t_{DH}$	0	-	0	-	0	-	0	-	ns
Output Active from End of Write	$t_{OW}^*$	3	-	3	-	3	-	3	-	ns
Write to Output in High Z	$t_{WHZ}^*$	-	4	-	5	-	6	-	7	ns
$\overline{LB}$ , $\overline{UB}$ Valid to End of Write	$t_{BW}$	7	-	8	-	9	-	10	-	ns

\*These parameters are guaranteed by device characterization, but not production tested.

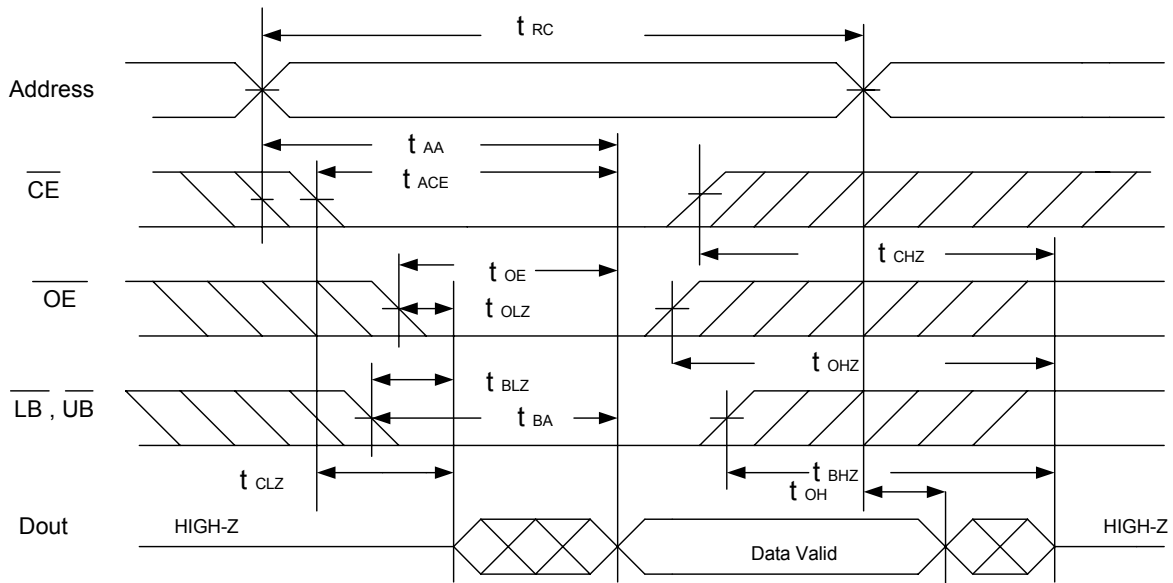


TIMING WAVEFORMS

READ CYCLE 1 (Address Controlled) (1,2,4)



READ CYCLE 2 ( $\overline{CE}$  and  $\overline{OE}$  Controlled) (1,3,5,6)

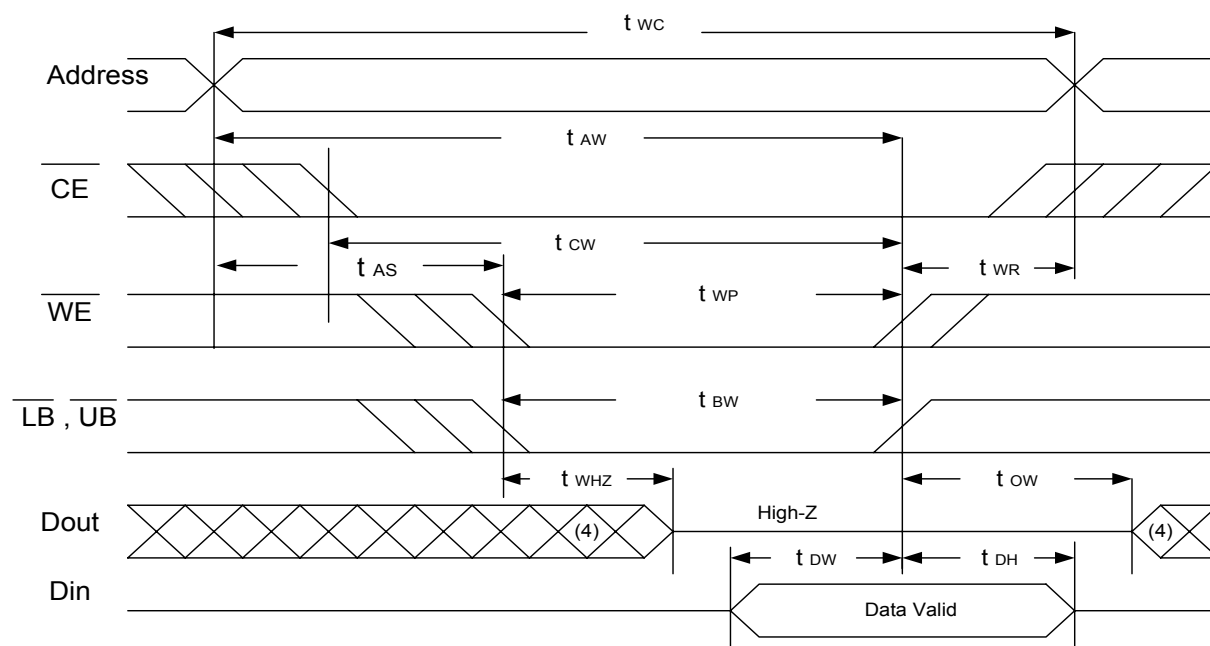


Notes :

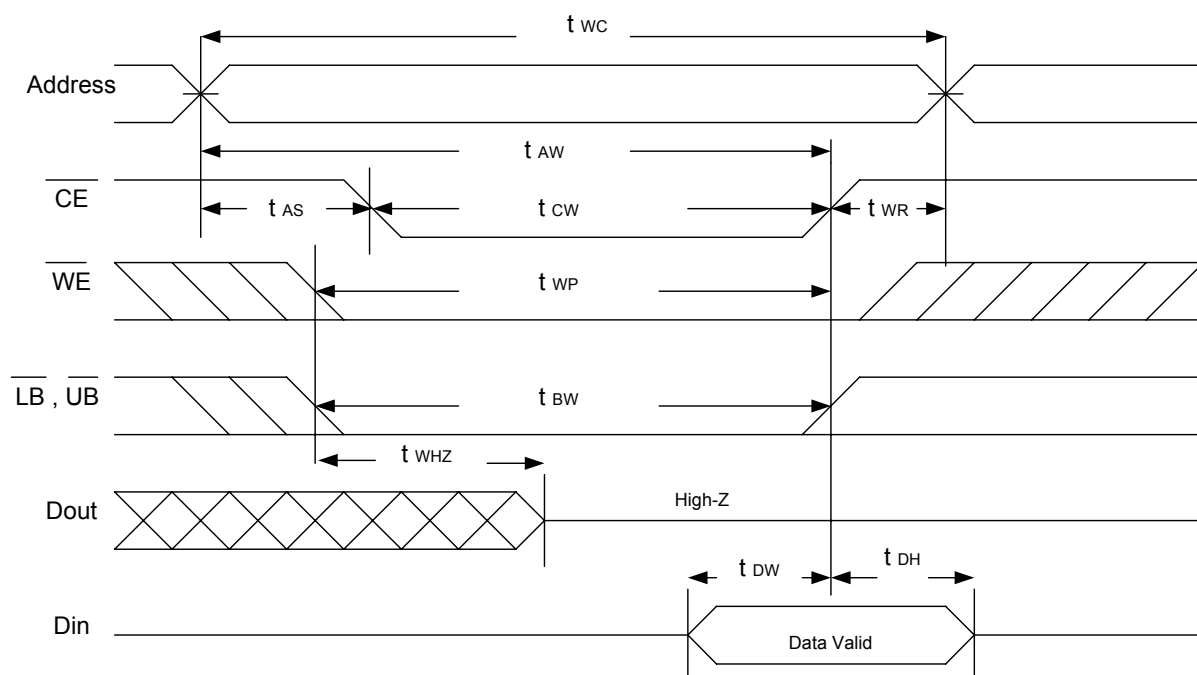
1.  $\overline{WE}$  is HIGH for read cycle.
2. Device is continuously selected  $\overline{CE} = V_{IL}$ .
3. Address must be valid prior to or coincident with  $\overline{CE}$  transition; otherwise  $t_{AA}$  is the limiting parameter.
4.  $\overline{OE}$  is LOW.
5.  $t_{CLZ}$ ,  $t_{OLZ}$ ,  $t_{CHZ}$ ,  $t_{OHZ}$ ,  $t_{BHZ}$  and  $t_{BLZ}$  are specified with  $C_L = 5pF$ . Transition is measured  $\pm 500mV$  from steady state.
6. At any given temperature and voltage condition,  $t_{CHZ}$  is less than  $t_{CLZ}$ ,  $t_{OHZ}$  is less than  $t_{OLZ}$ ,  $t_{BHZ}$  is less than  $t_{BLZ}$ .



WRITE CYCLE 1 ( $\overline{WE}$  Controlled) (1,2,3,5,6)



WRITE CYCLE 2 ( $\overline{CE}$  Controlled) (1,2,5)



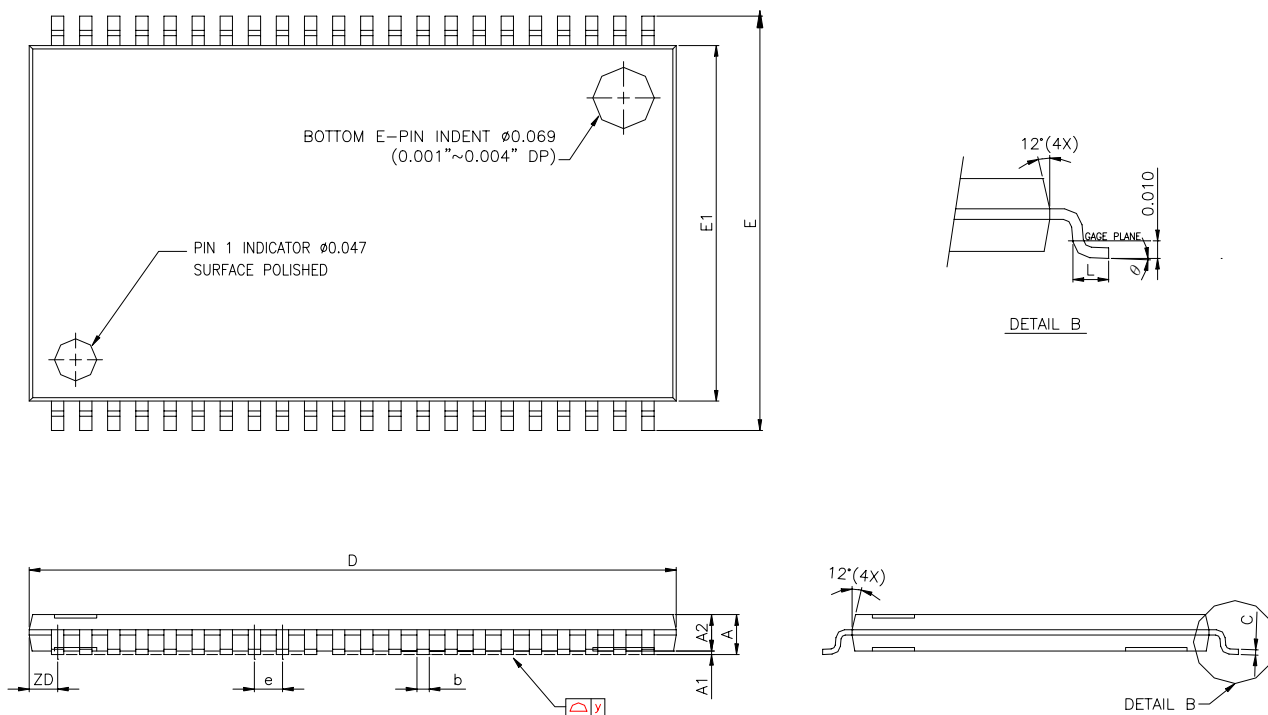
Notes :

1.  $\overline{WE}$  and  $\overline{CE}$  must be HIGH during all address transitions.
2. A write occurs during the overlap of  $\overline{CE} = \text{low}$ ,  $\overline{WE} = \text{low}$ ,  $\overline{LB}$  and/or  $\overline{UB} = \text{low}$ .
3. During a  $\overline{WE}$  controlled with write cycle with  $\overline{OE} = \text{LOW}$ ,  $t_{WP}$  must be greater than  $t_{WHZ} + t_{DW}$  to allow the drivers to turn off and data to be placed on the bus.
4. During this period, I/O pins are in the output state, and input signals must not be applied.
5. If the  $\overline{CE}$  low transition occurs simultaneously with or after  $\overline{WE}$  low transition, the outputs remain in a high impedance state.
6.  $t_{OW}$  and  $t_{WHZ}$  are specified with  $C_L = 5\text{pF}$ . Transition is measured  $\pm 500\text{mV}$  from steady state.



**PACKAGE OUTLINE DIMENSION**

**44-pin 400mil TSOP-II PACKAGE OUTLINE DIMENSION**



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHS		
	MIN	NOM	MAX.	MIN.	NOM.	MAX.
A	1.00	-	1.20	0.039	-	0.047
A1	0.05	-	0.15	0.002	-	0.006
A2	0.95	1.00	1.05	0.037	0.039	0.041
b	0.30	0.35	0.45	0.012	0.014	0.018
c	0.12	-	0.21	0.0047	-	0.083
D	18.313	18.415	18.517	0.721	0.725	0.728
E	11.854	11.836	11.838	0.460	0.466	0.470
E1	10.058	10.180	10.282	0.398	0.400	0.404
e	-	0.800	-	-	0.0315	-
L	0.40	0.50	0.60	0.0157	0.020	0.0236
2D	-	0.805	-	-	0.0317	-
y	0.00	-	0.076	0.000	-	0.003
θ	0°	-	5°	0°	-	5°



Rev. 1.0

UTRON

UT61L6416

64K X 16 BIT HIGH SPEED CMOS SRAM

**ORDERING INFORMATION**

**COMMERCIAL TEMPERATURE**

<b>PART NO.</b>	<b>ACCESS TIME (ns)</b>	<b>PACKAGE</b>
UT61L6416MC-8	8	44 PIN TSOP- II
UT61L6416MC-10	10	44 PIN TSOP- II
UT61L6416MC-12	12	44 PIN TSOP- II
UT61L6416MC-15	15	44 PIN TSOP- II





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